RD 51 Mini Week

November 2011

Gas gain in a single GEM: charge deposited on the dielectric

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- Difference between experimental and simullated GEM gain
- Charging-up effect on electric field and on gain
- Work status (simulations)
- Conclusions and Future Work

EXPERIMENTAL DATA (EL)





- Experimental parameters*:
 - Pure Xenon at 300K
 - Pression 1-2.5 bar
 - □ △VGem 200-600V

*C. M. B. Monteiro, A. S. Conceição, F. D. Amaro, J. M. Maia, A. C. S. S. M. Bento, L. F. R. Ferreira, J. F. C. A. Veloso, J. M. F. dos Santos, A. Breskin, e R. Chechik. Secondary scintillation yield from gaseous micropattern electron multipliers in direct Dark Matter detection. Phys. Lett. B, 677:133, 2009.

EXPERIMENTAL VS SIMULATED



POSSIBLE EXPLANATION

- Charging-up in the kapton surface
- The kapton surface goes from -25µm to +25µm

- Some electrons end on the surface of the kapton!
- Changes the local Electric field



SIMULLATIONS WITH CHARGING-UP

Our simullations were done with:

Primary electrons starts with z=200µm above the GEM

□ Voltage of VGEM=400V

Pression at 1 bar (760 torr)

Temperature of 293K

Method



FINAL POSITION OF ELECTRONS

□ At the end of each iteration, the electrons ending with z between -25µm and +25µm are counted

□ The upper surface (0 < z < 25µm) and the lower surface (-25µm < z < 0µm) of the kapton are studied independently (remember slide 5)</p>

Finally, the correspondent charge density of each surface is added (to the field map) and a new set of avalanches is simulated

Results



More electrons in the lower surface than in the upper (<u>slide 5</u>)

 Decreasing of the charge accumulation with time (electric repulsion)

Results



Initial increase of absolute gain (in charge and in light), followed by a drop!

EXPLANATIONS



CHANGES IN THE ELECTRIC FIELD



Only points with E larger than 400 Vcm⁻¹ are shown

Animation attached in the file "Efield.avi"

CHANGES IN THE ELECTRIC FIELD



- (logarithm) Intensity of the Electric Field increase in the lower electrode and decrease in the upper
- Increase also along the center of the hole

POSITIONS OF IONIZATIONS



- Remember <u>slide 10</u>, the increase until Npe=40x10⁴ followed by the drop
- Electrons are created later in the hole!

Iteration	lonizations Mean position
0	-21.89 μm
40	- 22 .31 μm
70	-23.38 μm
100	-24.47 μm

EXPLANATION

The increase of the electric field along the center of the hole is responsable for the initial increase of ionizations

Later, the decrease of the electric field in the upper electrodes will give less energy to the electrons, therefore they will produce less secundary electrons in initial states

The Ionizations starts later in the hole!

EXPLANATION

The process of avalanches is exponential - a few less electrons at the beginning will imply a significant lower gain



CONCLUSIONS



Is important to include it in simullations!



- In these simullations, we assume that the electrons simply "wait" in the kapton surface for ever. That it is not true.
- Over some time, the electrons should escape from the kapton (through the surface).
- □ We also didn't considerer the ion deposition in the kapton.
- Once the trapped ions gets close to trapped electrons, recombination can happen.

FUTURE WORK

Simultion of the charging-up for other gases (Ar/CO2) - currently running - results are expected soon

Implement the possible electrons mobility through the kapton

Ion contribution:

- □ Study the ion charging-up
- Study the possible recombination between trapped ions and electrons
- Study another Micro-Pattern Gaseous Detectors

END

Thank you for your attention.